

The Effect of Spin-Splitting on the Metallic Behavior of a Two-Dimensional System

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Experiments on a constant-density two-dimensional hole system in a GaAs quantum well reveal that the metallic behavior observed in the zero-magnetic-field temperature dependence of the resistivity depends on the symmetry of the confinement potential and the resulting spin-splitting of the valence band.

For many years, it was widely accepted that there can be no metallic phase in a disordered two-dimensional (2D) carrier system. This was due to the scaling arguments of Abrahams et al. [1], and the support of subsequent experiments [2]. In the last few years, however, experiments on high quality 2D systems have provided us with reason to re-visit the question of whether or not a metallic phase in a 2D system can exist [3–9]. Early temperature dependence data by Kravchenko et al., from high-mobility silicon metal-oxide-semiconductor field effect transistors (MOSFETs), showed a drop in resistivity as the temperature (T) was reduced below 2 K. This metallic behavior is the opposite of the expected insulating behavior in which the resistivity should become infinite as T approaches zero. In addition, the behavior not only was metallic in a certain electron density range, but also scaled with a single parameter as the density was reduced and the sample became insulating, suggesting a true metal-insulator phase transition [3].

Since these experiments, the metallic behavior has been observed in Si MOSFETs [3,4], SiGe quantum wells [5,6], GaAs/AlGaAs heterostructures [7,8], and AlAs quantum wells [9], demonstrating that there are still some unsolved puzzles in the fundamental nature of 2D carrier systems. Multiple mechanisms including electron-electron interaction [10], spin-splitting [11], and temperature dependence of traps [12] have been proposed as causes for the metallic behavior, but no clear model has emerged which fully describes this sizeable body of experimental data. The experiments reported here add to our understanding by demonstrating a correlation between the zero-magnetic-field spin-splitting and the metallic behavior.

Spin-splitting of carriers in a 2D system at zero magnetic field is caused by the spin-orbit interaction and by an inversion asymmetry of the potential in which the carriers move [13]. The energy bands are split into two spin-subbands, which have different populations because their energies at any non-zero $\vec{k}$ are slightly different. The ex-

istence of these spin-subbands has been well established both experimentally and theoretically [13–18].

Our experiments are performed on high-mobility 2D hole systems in GaAs quantum wells (QWs), chosen because they have a large inter-carrier separation r_s [19], have already shown metallic behavior [7,8], and exhibit a large and tunable spin-splitting [17]. In GaAs, the spin-splitting arises from the inversion asymmetries of the zincblende crystal structure and of the potential used to confine the electrons to two dimensions. The asymmetry of the crystal structure is fixed, but the asymmetry of the confining potential, and therefore the spin-splitting, can be changed by applying an $\vec{E}$ perpendicular to the 2D plane ($E_\perp$) using gates [17]. Firstly we demonstrate that the spin-splitting can be tuned while the density is kept constant, and then show that the metallic behavior of the 2D holes is related to the amount of spin-splitting observed.

Our samples are Si modulation doped, 200 Å-wide QWs grown by molecular beam epitaxy on the (311)A surface of an undoped GaAs substrate. QWs grown on the (311) surface of GaAs exhibit a mobility anisotropy believed to be caused by anisotropic interface roughness scattering [20]. Photolithography is used to pattern L-shaped Hall bars that allow simultaneous measurement of the resistivities along both the high-mobility ([233]) and low-mobility ([011]) directions. The samples have metal front and back gates that control both the 2D hole density and $E_\perp$. Measurements are done in a dilution refrigerator at temperatures from 0.7 K to 25 mK and in perpendicular magnetic fields (B) up to 16 T. We use the low-frequency lock-in technique, with a current of 10 nA, to measure the longitudinal (ρ) and Hall resistivities.

To measure the spin-splitting we examine the low- B ρ , or Shubnikov-de Haas (SdH), oscillations [16–18]. The frequencies of these oscillations, when multiplied by the level degeneracy e/h , give the spin-subband densities, which are a measure of the zero- B spin-splitting. To tune the splitting, we set the front gate (V_{fg}) and back gate (V_{bg}) voltages, and measure the resistivities as a function of B on both arms of the Hall bar. Then, at a small B , V_{fg} is increased and the change in the hole density noted. V_{bg} is then reduced to recover the original density. This procedure changes $E_\perp$ while maintaining the same density to within 1%, and allows calculation of the change in $E_\perp$ from the way the gates affect the density. These

steps are repeated until we have probed the range of V_{fg} and V_{bg} that are accessible without causing gate leakage. This is done for two samples, from different wafers, at 2D hole densities of $2.3 \times 10^{11} \text{ cm}^{-2}$ ($r_s = 6.8$) and $3.3 \times 10^{11} \text{ cm}^{-2}$ ($r_s = 5.7$) [19]. These densities place the samples well into the metallic regime [7,8]. The 25 mK mobilities of the two samples are 83 and 51 m^2/Vs for the [233] direction and 72 and 33 m^2/Vs for the [011] direction respectively. The results from both samples are similar.

Some of the low- B ρ data are shown (Fig. 1A) at a density of $3.3 \times 10^{11} \text{ cm}^{-2}$, from both the low- and high-mobility directions for various sets of V_{fg} and V_{bg} . The top trace was taken with the sample at a large positive $E_\perp$ (roughly 5,000 V/cm pointing towards the front gate). $E_\perp$ is reduced for the second trace, nearly zero in the middle trace, and increasingly negative in the next two traces (it is about -6,000 V/cm in the bottom trace). The frequencies (f_{SdH}) of the SdH oscillations are extracted by Fourier transforming the ρ vs. B^{-1} data in the range below 0.9 T. The Fourier transforms of the low-mobility data, (Fig. 1B), reveal how the spin-splitting changes as $E_\perp$ is changed from positive, through zero, to negative. From the symmetry of the data in Fig. 2A, we estimate that $E_\perp = 0$ is near $V_{fg} = -0.5$ V.

The next part of the experiment involves measuring the T dependence of ρ at $B = 0$ from 25 mK to about 0.7 K. In the data from the low mobility direction (Fig. 1C), the traces are separated vertically and displayed next to the corresponding Fourier transforms in Fig. 1B for clarity. Their ρ values at 25 mK and $B = 0$ (ρ_0) are shown on the y -axis. The most striking feature is that the T dependence of the $B = 0$ resistivity is larger when the two f_{SdH} peaks are well separated and smaller when there is no separation. It is clear that the magnitude of the T dependence is correlated with that of the spin-splitting. In order to characterize this data in a simple way we plot $\Delta\rho^T/\rho_0$, the fractional change in ρ from 25 mK to 0.67 K (Fig. 2B). Figs. 2A and 2B clearly show that ρ increases more strongly with T as the difference between the SdH frequencies (Δf_{SdH}) is increased. The same is true of the lower density sample. Additionally, $\Delta\rho^T/\rho_0$ is larger for lower density, consistent with previous experiments on the metallic behavior [3–9].

Finally, we attempt to more quantitatively determine what the temperature dependence would be in the limit of zero spin-splitting. To this end, we have performed simulations using self-consistent subband calculations that have no adjustable parameters [17]. They provide, for a given 2D hole density and $E_\perp$, both simulated SdH oscillations and the zero- B spin-subband population difference (Δp_s). Fourier transforms of the simulated SdH oscillations show peak positions that agree very well with those from the experimental data. Furthermore, while the sum of the f_{SdH} multiplied by e/h gives the total density, the calculations show that the Δf_{SdH} underestimates the zero- B Δp_s at all $E_\perp$. In particular, the sim-

ulations predict a finite zero- B spin-splitting at $E_\perp = 0$ (caused by the inversion asymmetry of the GaAs crystal structure), while for $|E_\perp| < 1000 \text{ V/cm}$ the Fourier transforms of the simulated SdH oscillations and of the experimental data show only one peak. The measured $\Delta\rho^T/\rho_0$ are plotted vs. the calculated Δp_s (Fig. 3) with the data for positive and negative $E_\perp$ separated on either side of the x -axis zero for clarity. These results suggest that $\Delta\rho^T/\rho_0$ would be zero or less than zero in the limit of zero spin-splitting.

The data show clearly that the magnitude of $\Delta\rho^T/\rho_0$ increases with the magnitude of $E_\perp$, which directly affects the amount of spin-splitting. Another parameter that is affected by $E_\perp$ is the mobility. However, as the ρ_0 values on the y -axis of Fig. 1C show, the changes in mobility do not correlate with changes in $\Delta\rho^T/\rho_0$. For example, for three of the traces, ρ_0 remains steady at 58.3 $\Omega/\text{sq.}$, but $\Delta\rho^T/\rho_0$ changes. Additionally $\Delta\rho^T/\rho_0$ is large when the mobility is small, in contrast to the observation that the metallic behavior becomes more pronounced as the mobility is improved [4]. Also, the dependence of mobility on $E_\perp$ varies from sample to sample and along different mobility directions within each sample [21]. Thus it is very unlikely that the mobility variation is causing the changes in $\Delta\rho^T/\rho_0$.

There are striking differences between the data along the low- and high-mobility directions that add a new twist to this problem. While the behaviors with $E_\perp$ are qualitatively similar, $\Delta\rho^T/\rho_0$ is an order of magnitude smaller in the high-mobility direction. Additionally, the low-mobility direction ρ shows a strong positive magnetoresistance, not present in the high-mobility ρ , that saturates at ~ 0.1 T. Its magnitude at 25 mK, $(\Delta\rho^B/\rho_0) = [\rho(0.1 \text{ T}) - \rho(0 \text{ T})]/\rho_0$, is plotted (Fig. 2C) and is remarkably similar to $\Delta\rho^T/\rho_0$ in Fig. 2B, despite the different origins (B and T dependence). The difference in mobility for the two directions is believed to come from an anisotropic interface roughness scattering that is due to the interface morphology (see Ref. [20] and references therein). On the other hand, the Fourier transforms of the SdH oscillations show that the spin-splitting is the same in both directions, so it is clear that the changes in $\Delta\rho^B/\rho_0$ and $\Delta\rho^T/\rho_0$ are not due to spin-splitting alone. It is possible that the directional differences in the B - and T -dependencies of ρ are due to an interplay between the applied B -field or the spin-splitting and the anisotropic scattering mechanism in the sample. The precise nature of this interplay remains to be discovered. These observations point to the subtlety of the physics behind the metallic behavior in this system.

We observe that the magnitude of the temperature dependence of the resistivity (the metallic behavior) increases with the magnitude of the spin-splitting. Previous experiments in applied B fields have provided evidence that the spin of the carriers plays an important role in the metallic behavior. However, in these experiments

the B field, which increases the spin-splitting, quenches the metallic state [8,22]. This inconsistency is surprising, and we surmise that in relation to the metallic behavior there is some fundamental difference between the zero- B spin-splitting, which is caused by the GaAs band structure and the confinement potential, and the non-zero- B spin-splitting, which is the difference in energy between carriers with spins parallel and anti-parallel to the applied B field [23]. Furthermore, our results point out a complication in experiments that examined the dependence of the metallic behavior on the carrier density: they were changing the spin-splitting as they changed the density [3–9]. Recognition of the fact that the zero- B spin-splitting is on its own important will help untangle the causes of this unexpected phenomenon. Finally, we note that there are significant differences between the low- and high-mobility direction data which have been overlooked in previous experiments on GaAs 2D holes. These differences may also provide clues to nature of the metallic behavior.

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FIG. 1. A: Magnetoresistance traces, all at a density of $3.3 \times 10^{11} \text{ cm}^{-2}$, but at different values of $E_{\perp}$. The data shown are from the low-mobility $[01\bar{1}]$ (upper trace in each box) and high-mobility $[\bar{2}33]$ directions. B: Fourier transforms of the Shubnikov-de Haas oscillations, showing that the spin-splitting is being tuned through a minimum. C: Temperature dependence of ρ for the low-mobility direction. The traces are shifted vertically for clarity, with the value of ρ at 25 mK listed along the y -axis for each trace. Each ρ vs. T trace is aligned with its corresponding Fourier transform. B and C together show that the magnitudes of the spin-splitting and the temperature dependence are related.

FIG. 2. A: Measured Shubnikov-de Haas frequencies plotted as a function of V_{fg} . Each V_{fg} has a corresponding V_{bg} (top axis) that is used to keep the density constant but vary $E_{\perp}$. B: $\Delta\rho^T/\rho_0$ vs. V_{fg} . $\Delta\rho^T$ is the change in ρ from $T = 25$ mK to 0.67 K and ρ_0 is ρ at 25 mK and $B = 0$ T. C: $\Delta\rho^B/\rho_0$ vs. V_{fg} . $\Delta\rho^B$ is the change in ρ from $B = 0$ to 0.1 T at 25 mK.

FIG. 3. $\Delta\rho^T/\rho_0$ from the high density sample plotted vs. the calculated zero- B population difference of the spin-subbands.





